



### **40V Dual N-Channel Enhancement Mode MOSFET**

Voltage

40 V

Current

37 A

### **Features**

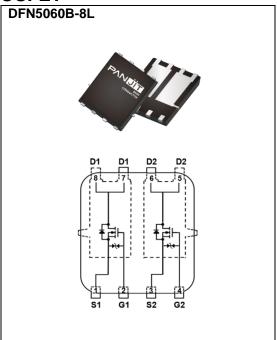
- RDS(ON), VGS@10V, ID@10A<12.3m $\Omega$
- RDS(ON), VGS@4.5V, ID@6A<15.7m $\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.092 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current(Note 3)	T <sub>C</sub> =25°C	l <sub>D</sub>	37	А	
	T <sub>C</sub> =100°C		26		
Pulsed Drain Current(Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	148		
Power Dissipation	T <sub>C</sub> =25°C	Po	30	W	
	T <sub>C</sub> =100°C		15		
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	10.6	^	
	T <sub>A</sub> =70°C		9	Α	
Power Dissipation	T <sub>A</sub> =25°C	,	2.5	W	
	T <sub>A</sub> =70°C	Po	1.8		
Single Pulse Avalanche Energy <sup>(Note 5)</sup>		Eas	42	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C	
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	$R_{ heta JC}$	5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60		





## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static	•						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =50uA	1.1	1.6	2.3		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	9.8	12.3	mΩ	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	12.1	15.7		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current		V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±10		
	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±1	uA	
Dynamic <sup>(Note 6)</sup>							
Total Gate Charge	Qg		-	13	-	nC	
Gate-Source Charge	Qgs	V <sub>DS</sub> =32V, I <sub>D</sub> =10A, V <sub>GS</sub> =10V	-	3	-		
Gate-Drain Charge	$Q_{gd}$	VGS=10V	-	2	-		
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	-	778	-	pF	
Output Capacitance	Coss		-	180	-		
Reverse Transfer Capacitance	Crss	I= IIVI⊓Z	-	25	-		
Gate resistance	Rg	f=1MHz	-	1.6	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>	\/ 00\/ L 40A	-	9	-		
Turn-On Rise Time	tr	V <sub>DS</sub> =32V, I <sub>D</sub> =10A,	-	3	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=10V, R_{G}=3\Omega$	-	21	-		
Turn-Off Fall Time	tf	(14016-2)	-	3	-		
Drain-Source Diode	_						
Diode Forward Current	Is	Tc=25°C	-	-	37	А	
Pulsed Diode Forward Current	I <sub>SM</sub>	10=25 C	-	-	148		
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V	-	0.9	1.3	V	
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	21	-	ns	
Reverse Recovery Charge	Qrr	dl <sub>S</sub> /dt=100A/us	-	10	-	nC	

### NOTES:

- 1. Pulse width<a></a>100us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R<sub>0JC</sub>=5°C/W.
- 4. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH,  $I_{AS}$ =13A,  $V_{DD}$ =30V,  $V_{GS}$ =10V, Starting  $T_{J}$ =25°C.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

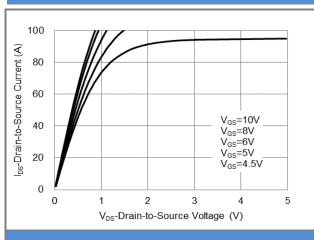
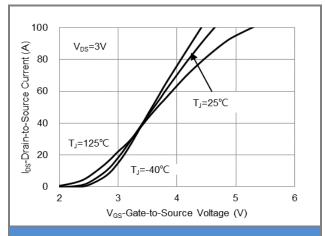


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

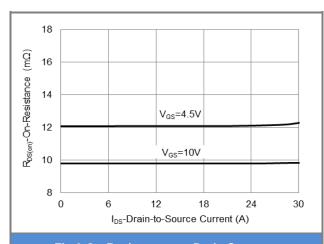


Fig.3 On-Resistance vs. Drain Current

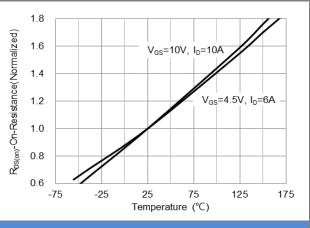


Fig.4 On-Resistance vs. Junction temperature

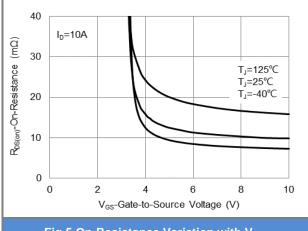


Fig.5 On-Resistance Variation with V<sub>GS</sub>

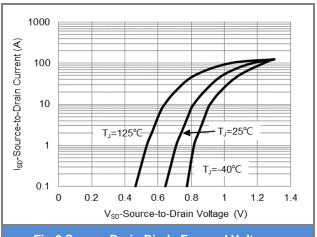


Fig.6 Source-Drain Diode Forward Voltage





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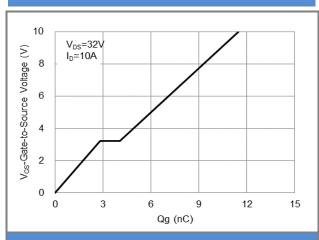


Fig.7 Gate-Charge Characteristics

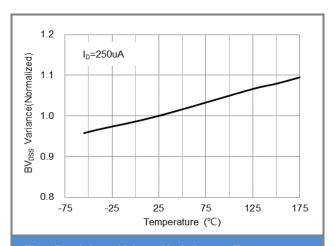


Fig.8 Breakdown Voltage Variation vs. Temperature

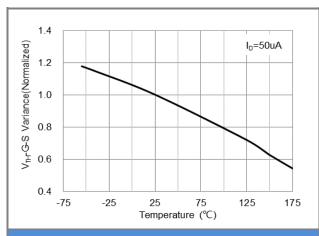


Fig.9 Threshold Voltage Variation with Temperature

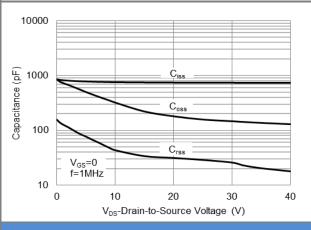
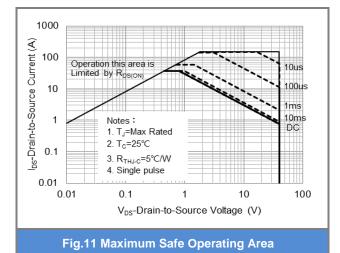


Fig.10 Capacitance vs. Drain-Source Voltage



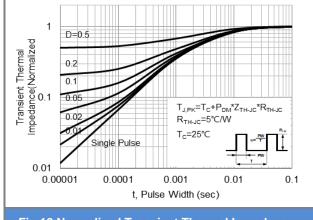


Fig.12 Normalized Transient Thermal Impedance

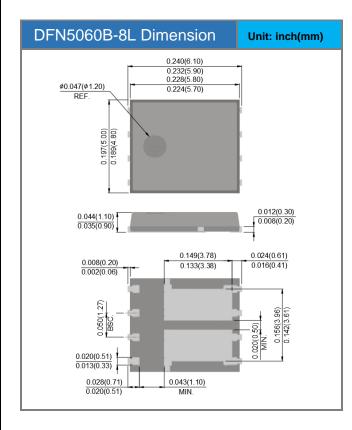


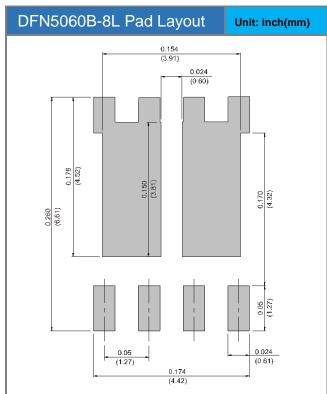


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ5948-AU	DFN5060B-8L	3K pcs / 13" reel	Q5948	

## **Packaging Information & Mounting Pad Layout**









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